

General description

These surge protection diodes are designed for applications requiring transient overvoltage protection capability. They are intended for use in voltage and ESD sensitive equipment such as computers, printers, business machines, communication systems, medical equipment and other applications. These devices are ideal for situations where board space is at a premium.

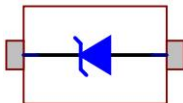
Features and benefits

- Working Voltage: 4.8V
- Response time is typically < 1 ns
- Low leakage current: nA Level
- IEC 61000-4-2 (ESD Air): $\pm 30\text{kV}$
- IEC 61000-4-2 (ESD Contact): $\pm 30\text{kV}$
- IEC 61000-4-5 (Lightning 8/20 μs): 170A

Application information

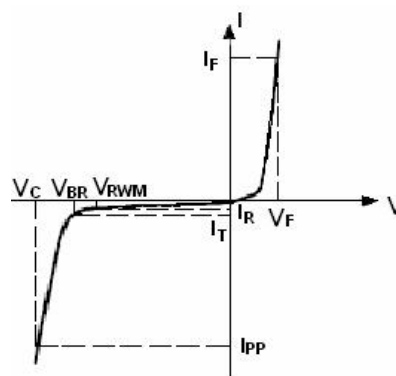
- Power lines
- Microprocessor based equipment
- Personal Digital Assistants (PDA's)
- Notebooks, Desktops, and Servers
- Cell phone Handsets and Accessories
- Portable Electronics

Schematic & Pin configuration

Simplified outline	Graphic symbol
	

Portion Electronics Parameter

Symbol	Parameter
I_{PP}	Reverse Peak Pulse Current
V_C	Clamping Voltage @ I_{PP}
V_{RWM}	Working Peak Reverse Voltage
I_R	Reverse Leakage Current @ V_{RWM}
V_{BR}	Breakdown Voltage @ I_T
I_T	V_{BR} Test Current
I_F	Forward Current
V_F	Forward Voltage @ I_F



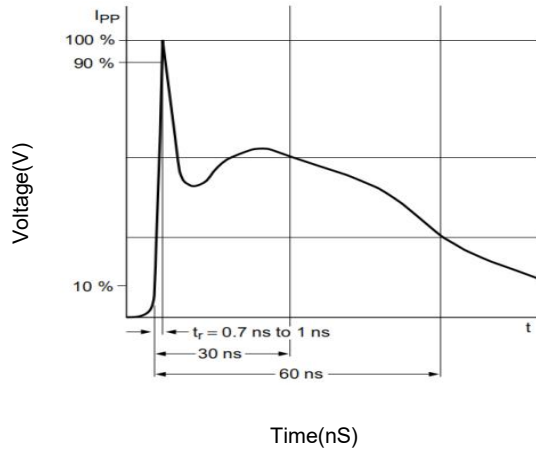
Maximum Ratings ($T_A = 25\text{ }^{\circ}\text{C}$, unless otherwise specified)

Parameter	Symbol	Value	Unit
Peak Pulse Power ($T_p = 8/20\mu\text{s}$)	P_{PPM}	2000	W
Rated Peak Pulse Current ($T_p = 8/20\mu\text{s}$)	I_{PPM}	170	A
ESD voltage IEC 61000-4-2 (air discharge)	V_{ESD}	30	kV
ESD voltage IEC 61000-4-2 (contact discharge)	V_{ESD}	30	kV
Maximum lead temperature for soldering during 10s	T_L	260	$^{\circ}\text{C}$
Storage Temperature Range	T_{stg}	-55 to +150	$^{\circ}\text{C}$
Operating Temperature Range	T_J	-40 to +125	$^{\circ}\text{C}$

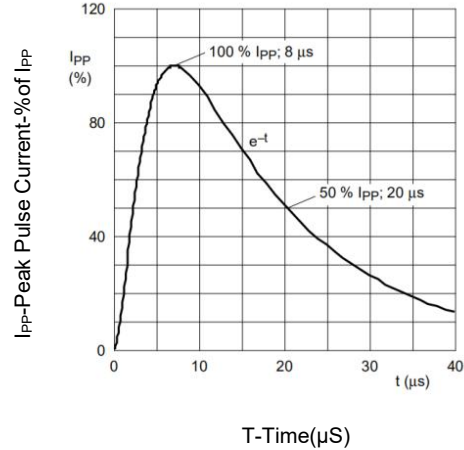
Electrical Characteristics ($T_A = 25\text{ }^{\circ}\text{C}$, unless otherwise specified)

Parameter	Symbol	Min	Typ	Max	Unit	Condition
Reverse Working Voltage	V_{RWM}	--	--	4.8	V	
Breakdown Voltage	V_{BR}	5.5	6.0	6.5	V	$I_T = 1\text{mA}$
Leakage Current I_{Leak}	I_R	--	--	100	nA	$V_{RWM} = 4.8\text{V}$
Forward Voltage	V_F	0.6	0.8	0.9	V	$I_F = 10\text{mA}$
Clamping Voltage	V_C	--	5.5	--	V	$I_{PP} = 1\text{A}, T_p = 8/20\mu\text{s}$
Clamping Voltage	V_C	--	10.4	11.8	V	$I_{PP} = 170\text{A}, T_p = 8/20\mu\text{s}$
Junction Capacitance	C_j	--	480	550	pF	$V_R = 0\text{V}, f = 1\text{MHz}$
Junction Capacitance	C_j	--	300	350	pF	$V_R = 4.8\text{V}, f = 1\text{MHz}$

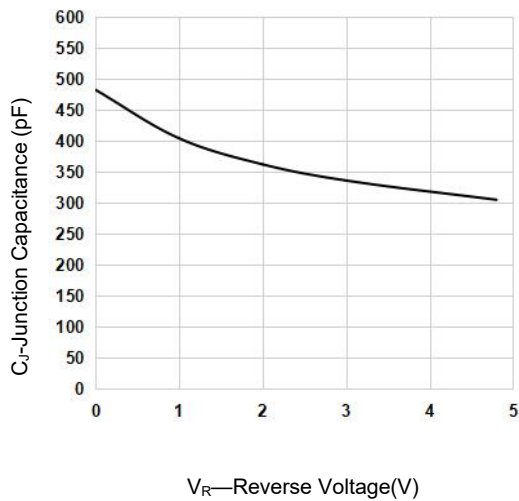
Typical Performance Characteristics ($T_A=25^{\circ}\text{C}$ unless otherwise Specified)



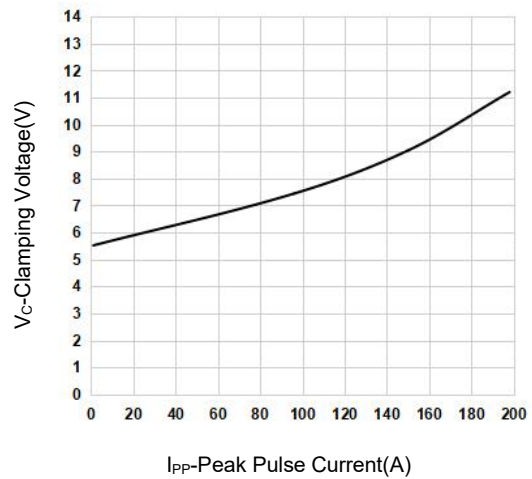
IEC61000-4-2 Pulse Waveform



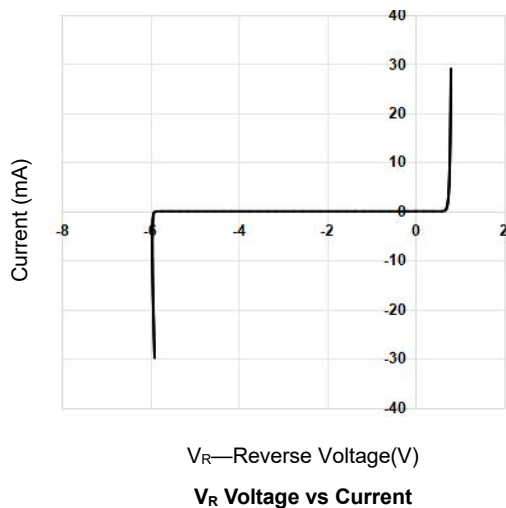
IEC61000-4-5 8X20 μs Pulse Waveform



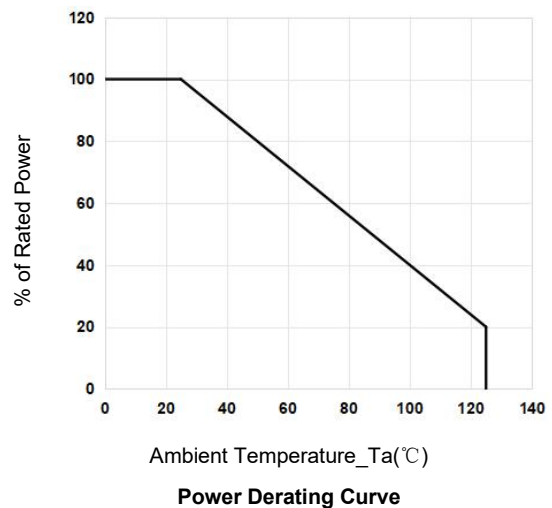
Junction Capacitance vs. Reverse Voltage



Clamping Voltage vs. Peak Pulse Current



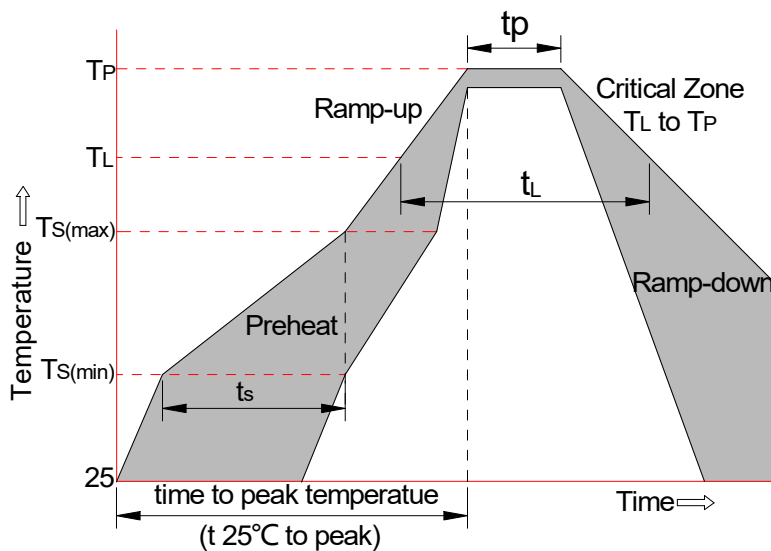
V_R Voltage vs Current



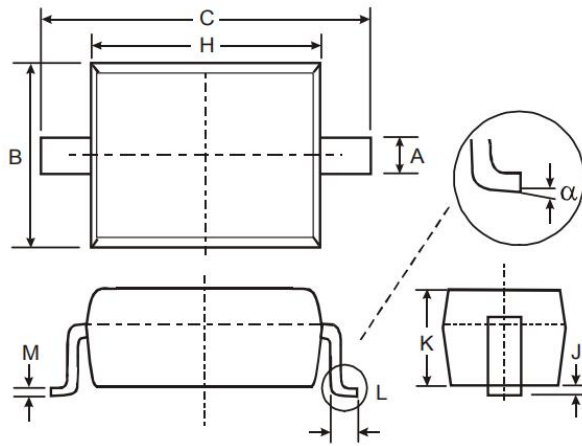
Power Derating Curve

Soldering Parameters

Reflow Condition		Pb-Free Assembly
Pre-heat	-Temperature Min ($T_{s(min)}$)	+150°C
	-Temperature Max($T_{s(max)}$)	+200°C
	-Time (Min to Max) (t_s)	60-180 secs.
Average ramp up rate (Liquid us Temp (T_L) to peak)		3°C/sec. Max
$T_{s(max)}$ to T_L - Ramp-up Rate		3°C/sec. Max
Reflow	-Temperature(T_L)(Liquid us)	+217°C
	-Temperature(t_L)	60-150 secs.
Peak Temp (T_p)		+260(+0/-5)°C
Time within 5°C of actual Peak Temp (t_p)		30 secs. Max
Ramp-down Rate		6°C/sec. Max
xTime 25°C to Peak Temp (T_p)		8 min. Max
Do not exceed		+260°C

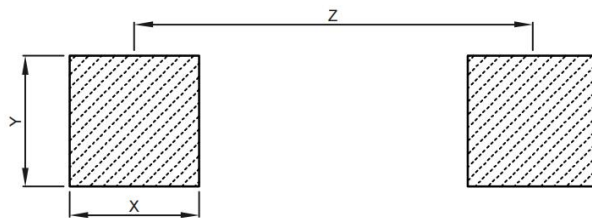


Package Outline Dimensions (SOD323)



SYMBOL	MILLIMETERS	
	MIN	MAX
A	0.25	0.35
B	1.20	1.40
C	2.40	2.70
H	1.60	1.80
J	0.01	0.15
K	0.70	0.90
L	0.20	0.40
M	0.08	0.15
α	0°	8°

Soldering Footprint (mm)



SYMBOL	MILLIMETERS	
	MIN	MAX
X	0.65	0.75
Y	0.65	0.75
Z	2.10	2.20

Ordering information

Package	Reel Size	Packaging (pcs)
SOD323	7 Inch	3000/Tape & Reel